



ON Semiconductor®

FQD13N06L / FQU13N06L

N-Channel QFET® MOSFET

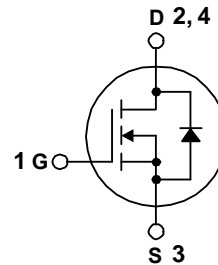
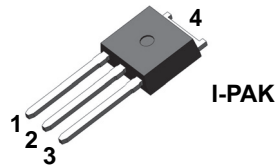
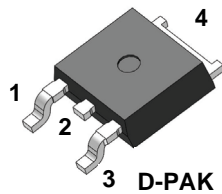
60 V, 11 A, 115 mΩ

Features

- 11 A, 60 V, $R_{DS(on)} = 115 \text{ m}\Omega$ (Max) @ $V_{GS} = 10 \text{ V}$, $I_D = 5.5 \text{ A}$
- Low Gate Charge (Typ. 4.8 nC)
- Low C_{rss} (Typ. 17 pF)
- 100% Avalanche Tested
- Low Level Gate Drive Requirements Allowing Direct Operation from Logic Drivers

Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQD13N06LTM / FQU13N06LTU FQU13N06LTU-WS	Unit
V_{DSS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	11	A
		7	A
I_{DM}	Drain Current - Pulsed (Note 1)	44	A
V_{GSS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	90	mJ
I_{AR}	Avalanche Current (Note 1)	11	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	2.8	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P_D	Power Dissipation ($T_A = 25^\circ\text{C}$) *	2.5	W
	Power Dissipation ($T_C = 25^\circ\text{C}$)	28	W
	- Derate above 25°C	0.22	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FQD13N06LTM FQU13N06LTU FQU13N06LTU-WS	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

FQD13N06L / FQU13N06L — N-Channel QFET® MOSFET

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD13N06LTM	FQD13N06L	D-PAK	Tape and Reel	330 mm	16 mm	2500 units
FQU13N06LTU	FQU13N06L	I-PAK	Tube	N/A	N/A	70 units
FQU13N06LTU-WS	FQU13N06LS	I-PAK	Tube	N/A	N/A	75 units

Electrical Characteristics $T_c = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.05	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 48\text{ V}, T_c = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0	--	2.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$	--	0.092	0.115	Ω
		$V_{GS} = 5\text{ V}, I_D = 5.5\text{ A}$	--	0.115	0.145	
g_{FS}	Forward Transconductance	$V_{DS} = 25\text{ V}, I_D = 5.5\text{ A}$	--	6	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	270	350	pF
C_{oss}	Output Capacitance		--	95	125	pF
C_{rss}	Reverse Transfer Capacitance		--	17	23	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 6.8\text{ A},$ $R_G = 25\ \Omega$	--	8	25	ns	
t_r	Turn-On Rise Time		--	90	190	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4)	--	20	50	ns
t_f	Turn-Off Fall Time		(Note 4)	--	40	90	ns
Q_g	Total Gate Charge	$V_{DS} = 48\text{ V}, I_D = 13.6\text{ A},$ $V_{GS} = 5\text{ V}$	--	4.8	6.4	nC	
Q_{gs}	Gate-Source Charge		(Note 4)	--	1.6	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4)	--	2.7	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	11	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	44	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 11\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 13.6\text{ A},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$	--	45	--	ns
Q_{rr}	Reverse Recovery Charge		--	45	--	nC

Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. $L = 870\ \mu\text{H}, I_{AS} = 11\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 13.6\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

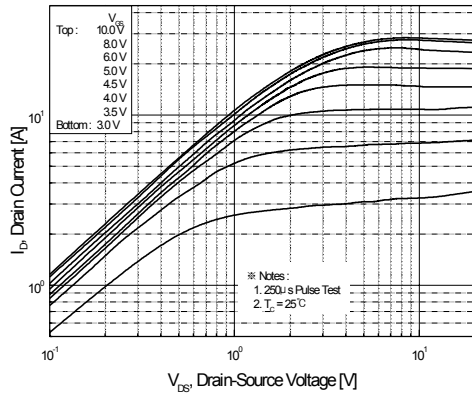


Figure 1. On-Region Characteristics

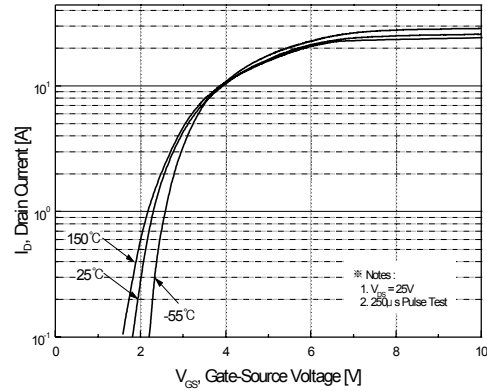


Figure 2. Transfer Characteristics

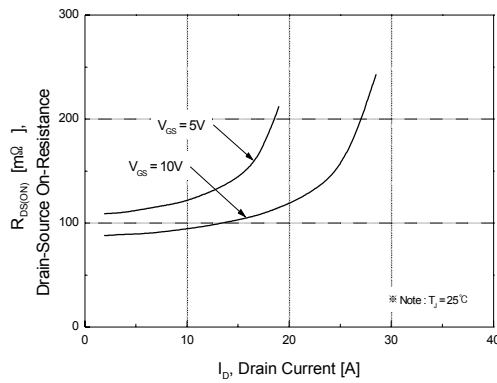


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

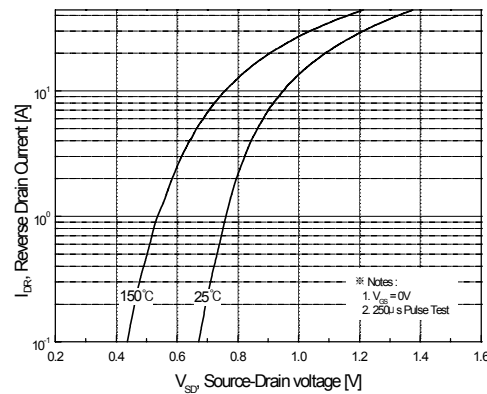


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

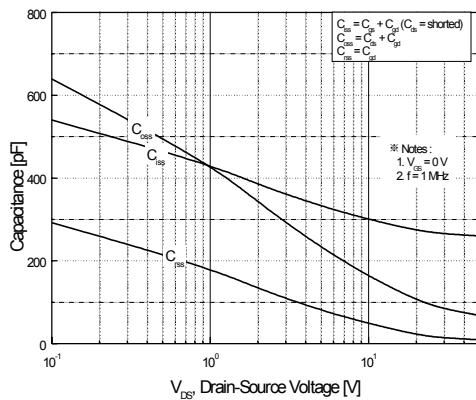


Figure 5. Capacitance Characteristics

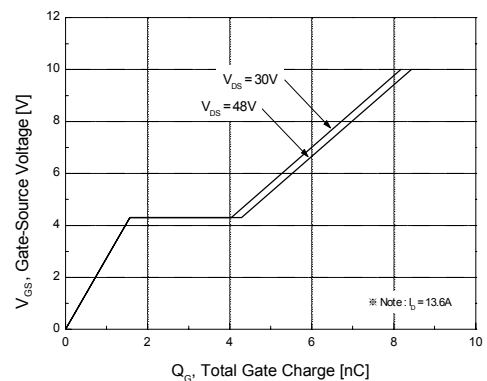


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

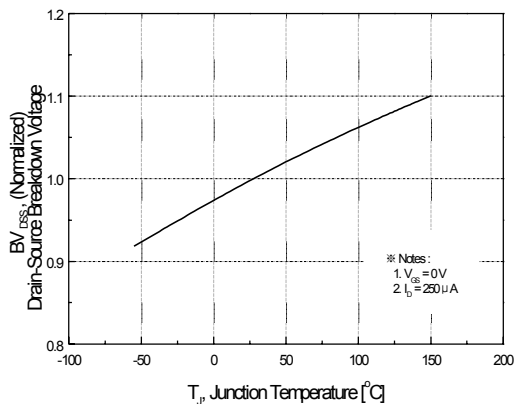


Figure 7. Breakdown Voltage Variation vs. Temperature

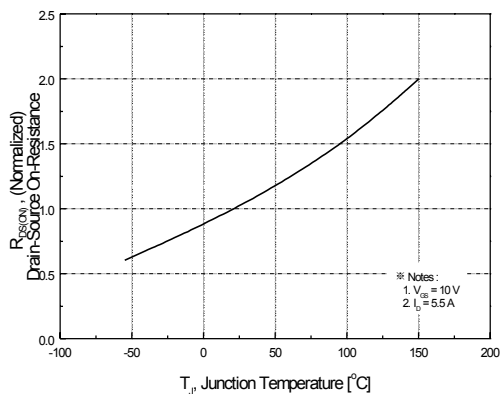


Figure 8. On-Resistance Variation vs. Temperature

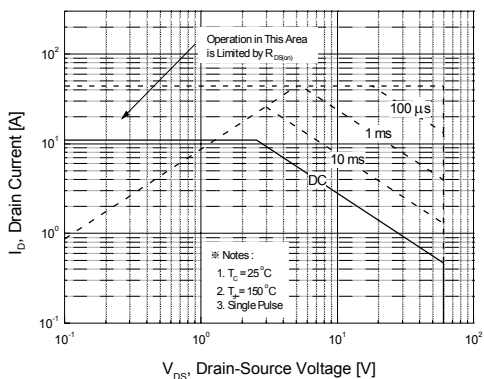


Figure 9. Maximum Safe Operating Area

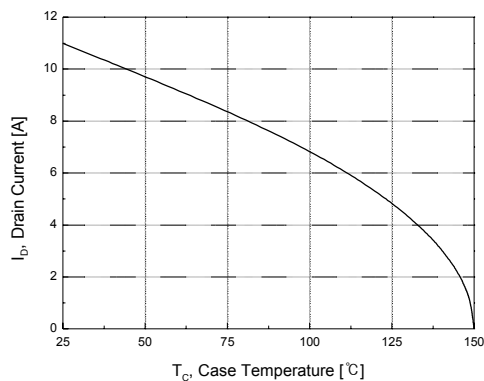


Figure 10. Maximum Drain Current vs. Case Temperature

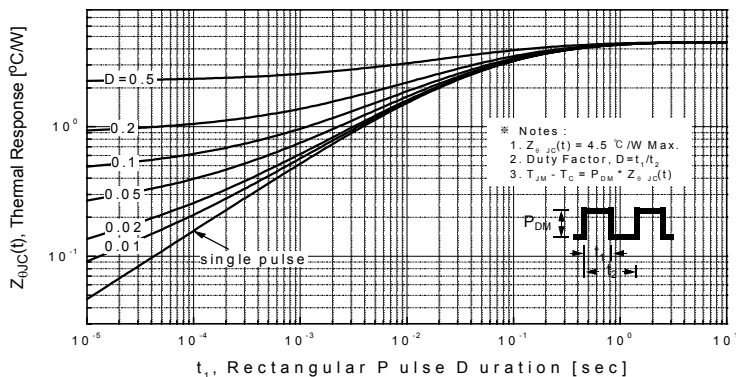


Figure 11. Transient Thermal Response Curve

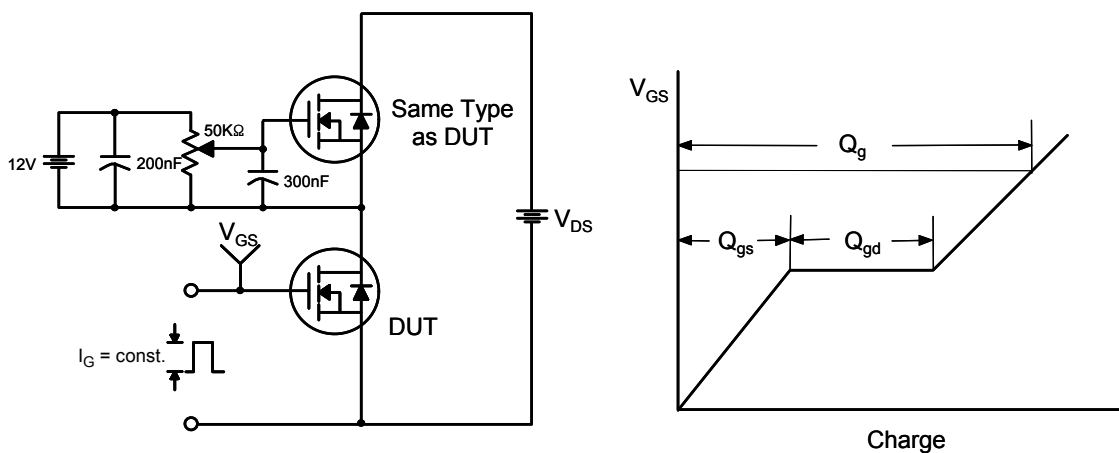


Figure 12. Gate Charge Test Circuit & Waveform

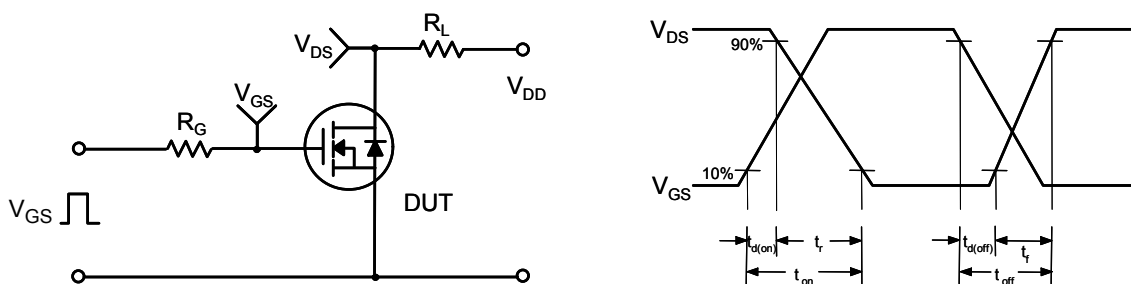


Figure 13. Resistive Switching Test Circuit & Waveforms

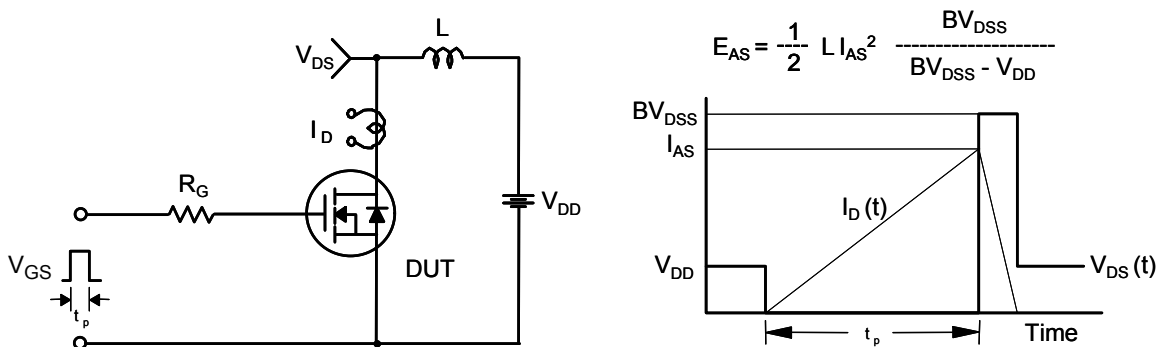


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

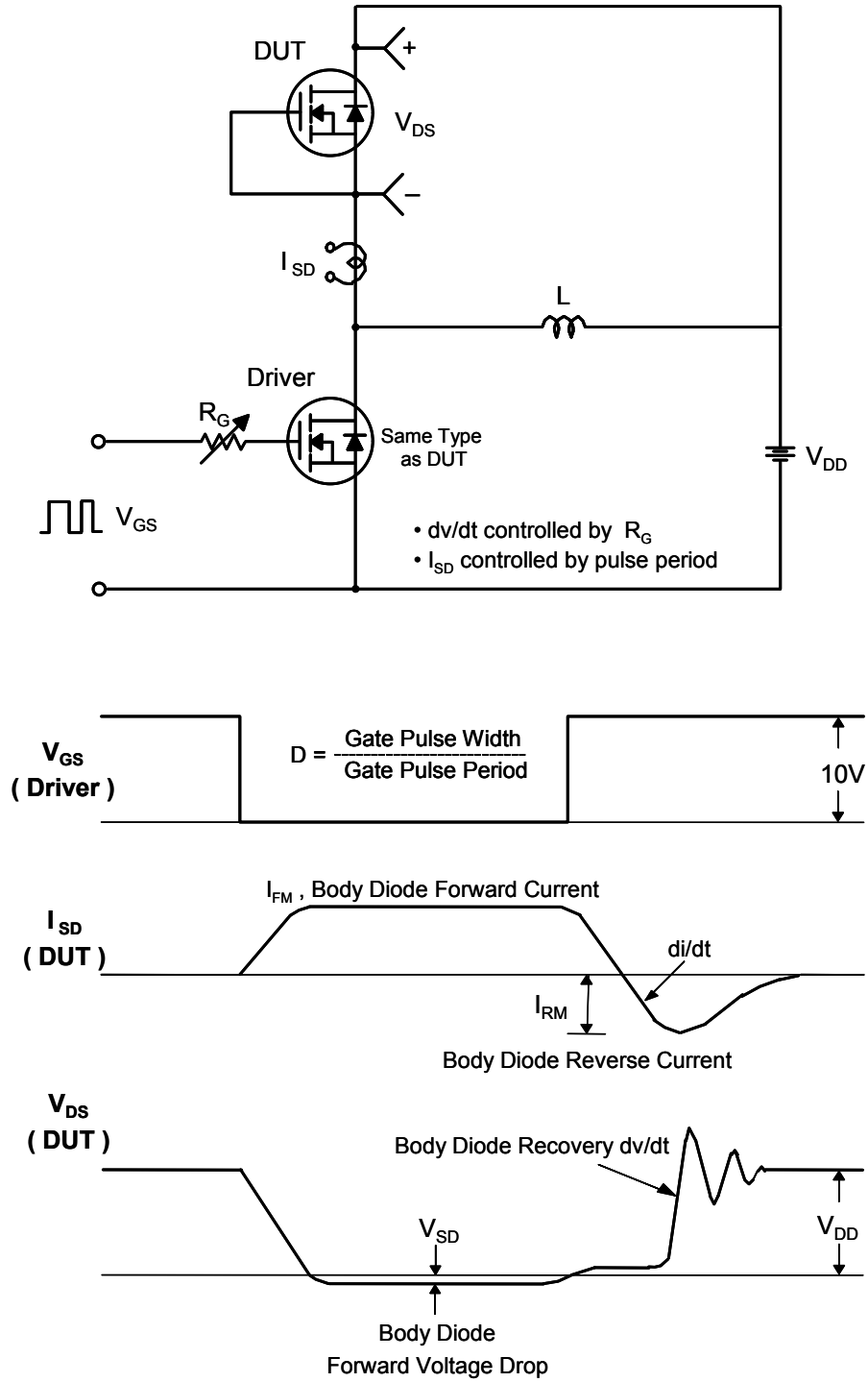
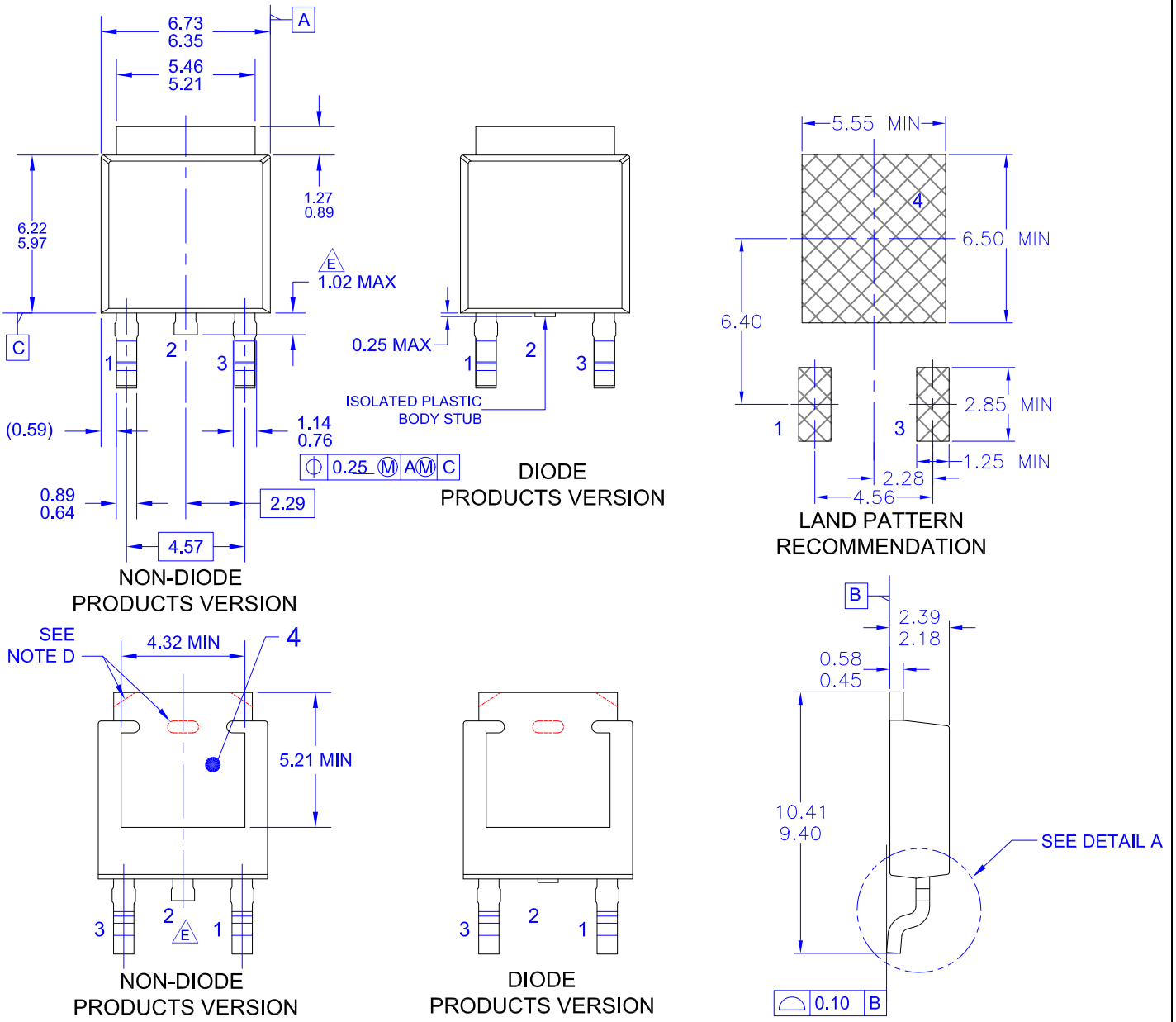
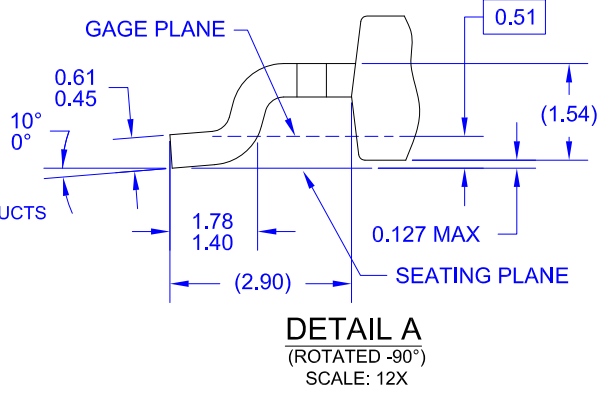


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

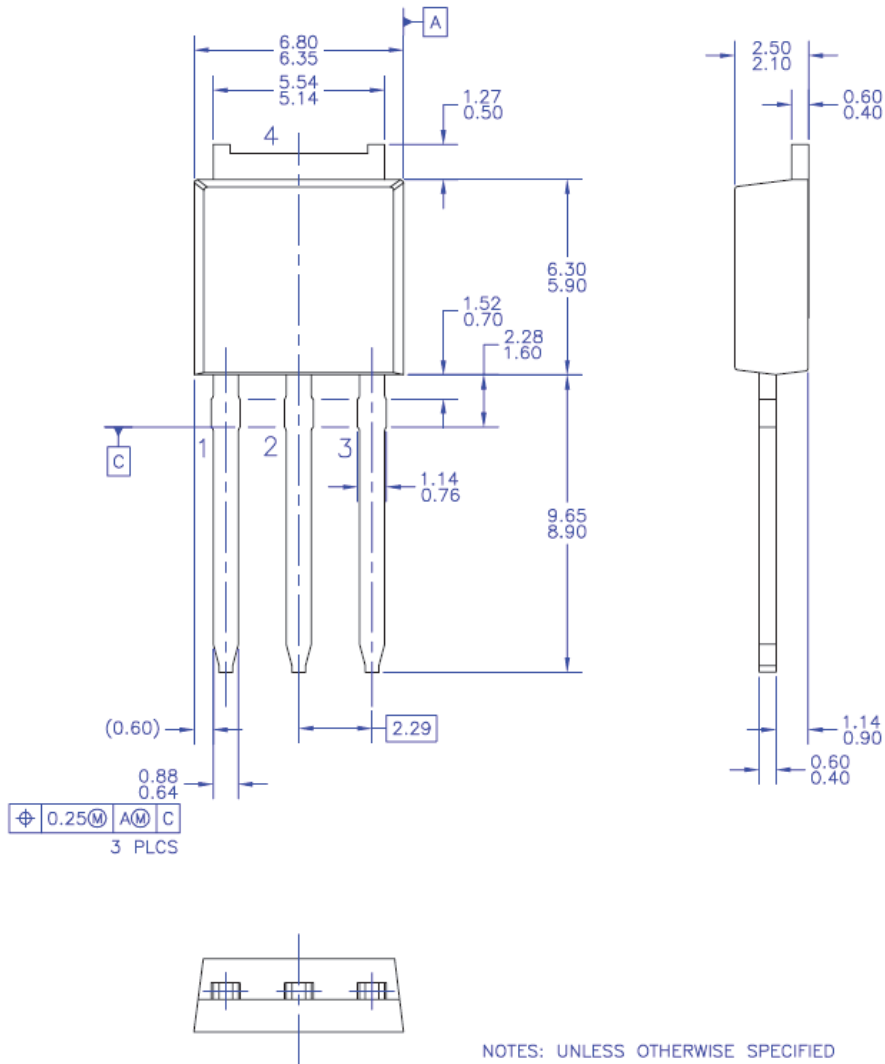


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 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
 - E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
 - F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
 - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
 - H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



Mechanical Dimensions

FQU13N06LTU



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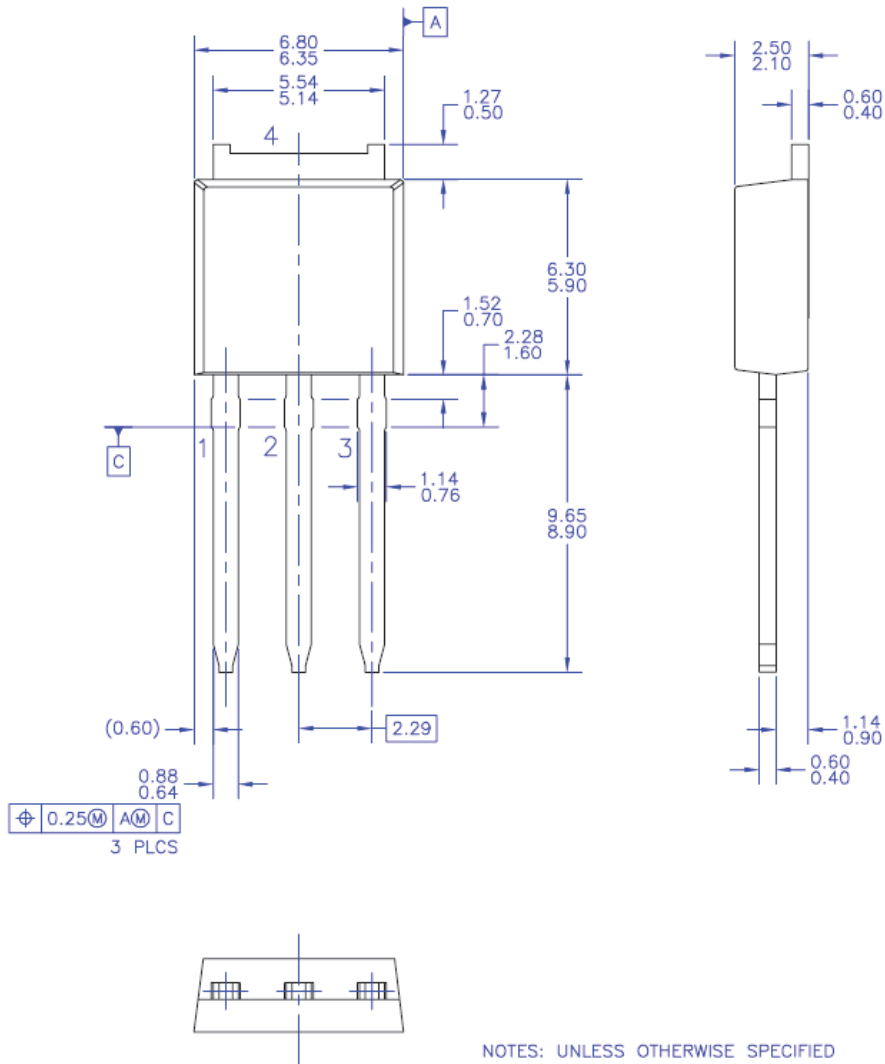
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Figure 17. TO251 (I-PAK), Molded, 3-Lead

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Mechanical Dimensions

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Figure 18. TO-251 (I-PAK), Molded, 3-Lead, Option AA

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